Elektronische Bauelemente

2SD886

3A , 50V

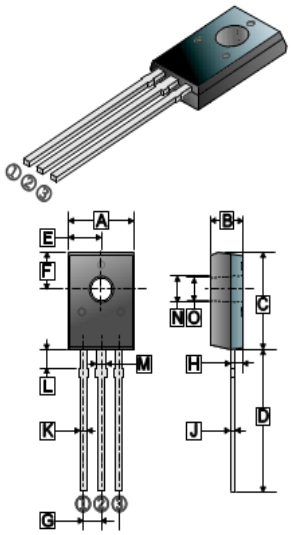
NPN Plastic Encapsulated Transistor

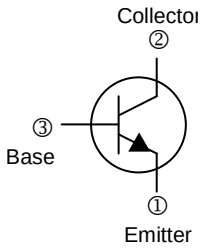
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Low frequency power amplifier
- High Current

TO-126





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	7.40	7.80	H	1.10	1.50
B	2.50	2.90	J	0.45	0.60
C	10.60	11.00	K	0.66	0.86
D	15.30	15.70	L	2.10	2.30
E	3.70	3.90	M	1.17	1.37
F	3.90	4.10	N	3.00	3.20
G	2.29 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	3	A
Maximum Junction to Ambient	$R_{\theta JA}$	125	℃ / W
Collector Power Dissipation	P_C	1	W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	50	-	-	V	I_C=100μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	50	-	-	V	I_C=5mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=100μA, I_C=0
Collector Cut – Off Current	I_{CBO}	-	-	1	μA	V_{CB}=50V, I_E=0
Emitter Cut – Off Current	I_{EBO}	-	-	1	μA	V_{EB}=3V, I_C=0
DC Current Gain [1]	h_{FE}	100	-	-		V_{CE}=2V, I_C=20mA
		100	-	400		V_{CE}=2V, I_C=1A*
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.5	V	I_C=2A, I_B=200mA
Base-emitter saturation voltage	$V_{BE(sat)}$	-	-	2	V	I_C=2A, I_B=200mA
Transition Frequency	f_T	-	80	-	MHz	V_{CE}=5V, I_C=100mA
Collector output capacitance	C_{ob}	-	45	-	pF	V_{CB}=10V, I_E=0, f=1MHz

Note:
1. Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.